

direct Wide Band Gap Diodes

Summary:

direct Wide Band Gap diodes are made from GaAs and are the next iteration of WBG materials bringing WBG performance and Si pricing together. GaAs is the second most used semiconductor material and therefore well known in production and applications for many years

Differentiation:

- Vf: better than SiC and Si semiconductor
- Super low junction Capacitance and higher carrier mobility compared to Si and SiC
- Higher (surge) current capability
- Cost effective compared to other WBG materials
- Lower losses in ZVS applications

Available products:

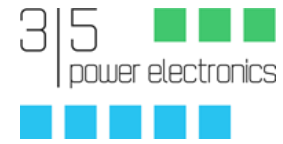
- 400V, 10A - 60A: bare die, TO247, D2PAK, SOT227
 - 650V, 10A - 60A: bare die, TO247, D2PAK, SOT227
 - 900V, 10A - 60A: bare die, TO247, D2PAK, SOT227
- Contact sales@foxypower.com for other packages and requests

Company description:

3-5 Power Electronics is a Dresden, Germany based company; founded in 2015 by executives of worldwide semiconductor companies, combining about 90 years of semiconductor industry expertise.

- ✓ Motor drives
- ✓ Power supplies
- ✓ Automotive
- ✓ Renewables

- ✓ Transportation
- ✓ Aerospace
- ✓ Server/Telecom
- ✓ Battery Charging



Applications:

Technical specifications:

Depending on product and customer requirements.

Further remarks:

Collaborating with AZUR SPACE , Germany, a global leader in development and production of multi junction solar cells for space applications based on GaAs semiconductor materials. Capacity of up to 500k wafers/ year.

